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| **1N4001** | **1N4002** | **1N4003** | **1N4004** |
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| **General Purpose Rectifier Diode** | **General Purpose Rectifier Diode** | **General Purpose Rectifier Diode** | **General Purpose Rectifier Diode** |
| **V**RRM = **50 V** VF at 1 A = **1.1 V**  IF(AV) at 75°C = **1 A**  IFSM (8.3 ms half sine-wave) = **30 A**  I2t for t < 8.3 ms = **3.7 A2sec**  IR at 25°C = **5 µA**  PD at 25 °C = **3 W**  TJ, TSTG = **-55 to 175 °C** RθJA = **50 °C/W** | VRRM = **100 V** VF at 1 A = **1.1 V**  IF(AV) at 75°C = **1 A**  IFSM (8.3 ms half sine-wave) = **30 A**  I2t for t < 8.3 ms = **3.7 A2sec**  IR at 25°C = **5 µA**  PD at 25 °C = **3 W**  TJ, TSTG = **-55 to 175 °C** RθJA = **50 °C/W** | VRRM = **200 V** VF at 1 A = **1.1 V**  IF(AV) at 75°C = **1 A**  IFSM (8.3 ms half sine-wave) = **30 A**  I2t for t < 8.3 ms = **3.7 A2sec**  IR at 25°C = **5 µA**  PD at 25 °C = **3 W**  TJ, TSTG = **-55 to 175 °C** RθJA = **50 °C/W** | VRRM = **400 V** VF at 1 A = **1.1 V**  IF(AV) at 75°C = **1 A**  IFSM (8.3 ms half sine-wave) = **30 A**  I2t for t < 8.3 ms = **3.7 A2sec**  IR at 25°C = **5 µA**  PD at 25 °C = **3 W**  TJ, TSTG = **-55 to 175 °C** RθJA = **50 °C/W** |
| **1N4005** | **1N4006** | **1N4007** | **1N5404** |
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| **General Purpose Rectifier Diode** | **General Purpose Rectifier Diode** | **General Purpose Rectifier Diode** | **General Purpose Rectifier Diode** |
| VRRM = **600 V** VF at 1 A = **1.1 V**  IF(AV) at 75°C = **1 A**  IFSM (8.3 ms half sine-wave) = **30 A**  I2t for t < 8.3 ms = **3.7 A2sec**  IR at 25°C = **5 µA**  PD at 25 °C = **3 W**  TJ, TSTG = **-55 to 175 °C** RθJA = **50 °C/W** | VRRM = **800 V** VF at 1 A = **1.1 V**  IF(AV) at 75°C = **1 A**  IFSM (8.3 ms half sine-wave) = **30 A**  I2t for t < 8.3 ms = **3.7 A2sec**  IR at 25°C = **5 µA**  PD at 25 °C = **3 W**  TJ, TSTG = **-55 to 175 °C** RθJA = **50 °C/W** | VRRM = **1000 V** VF at 1 A = **1.1 V**  IF(AV) at 75°C = **1 A**  IFSM (8.3 ms half sine-wave) = **30 A**  I2t for t < 8.3 ms = **3.7 A2sec**  IR at 25°C = **5 µA**  PD at 25 °C = **3 W**  TJ, TSTG = **-55 to 175 °C** RθJA = **50 °C/W** | VRRM = **400 V** VF at 3 A = **1.2 V**  IF(AV) at 75°C = **3 A**  IFSM (8.3 ms half sine-wave) = **200 A**  Irr at TA: 25°C= **0.5 mA**  IR at 25°C = **5 µA**  PD at 25 °C = **6.25 W**  TJ, TSTG = **-55 to 150 °C** RθJA = **20 °C/W** |
| **1N5406** | **1N5408** | **RL207** | **6A10** |
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| **General Purpose Rectifier Diode** | **General Purpose Rectifier Diode** | **General Purpose Rectifier Diode** | **Silicon Rectifier Diode** |
| VRRM = **600 V** VF at 3 A = **1.2 V**  IF(AV) at 75°C = **3 A**  IFSM (8.3 ms half sine-wave) = **200 A**  Irr at TA: 25°C = **0.5 mA**  IR at 25°C = **5 µA**  PD at 25 °C = **6.25 W**  TJ, TSTG = **-55 to 150 °C** RθJA = **20 °C/W** | VRRM = **1000 V** VF at 3 A = **1.2 V**  IF(AV) at 75°C = **3 A**  IFSM (8.3 ms half sine-wave) = **200 A**  Irr at TA: 25°C = **0.5 mA**  IR at 25°C = **5 µA**  PD at 25 °C = **6.25 W**  TJ, TSTG = **-55 to 150 °C** RθJA = **20 °C/W** | VRRM = **1000 V** VF at 2 A = **1 V**  VRMS = **700 A**  VDC = **1000 V**  IFSM (8.3 ms half sine-wave) = **70 A**  IO at TA: 75°C = **2 A**  IR at 25°C = **1 µA**  TJ, TSTG = **-55 to 150 °C** RθJA = **40 °C/W** | VRRM = **1000 V** VFM at 6 A = **0.9 V**  VRMS = **700 A**  VDC = **1000 V**  IFSM (8.3 ms half sine-wave) = **400 A**  I(AV) at TA: 75°C = **6 A**  IRM at 25°C = **10 µA**  TJ, TSTG = **-65 to 175 °C** |
| **10A10** |  |  |  |
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| **Silicon Rectifier Diode** |  |  |  |
| VRRM = **1000 V** VF at 10 A = **1.1 V**  VRMS = **700 V**  VDC = **1000 V**  IO at 75°C = **10 A**  IFSM (8.3 ms half sine-wave) = **400 A**  IR at 25°C = **5 µA**  TJ, TSTG = **-55 to 150 °C** RθJA = **20 °C/W** |  |  |  |
| **UF4007** | **FR107** | **FR207** | **1N4148** |
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| **Fast Recovery Rectifier Diode** | **Fast Recovery Rectifier Diode** | **Fast Recovery Rectifier Diode** | **Small Signal Fast Switching Diode** |
| VRRM = **1000 V** VF at 1 A = **1.7 V**  VRMS = **700 V**  VDC = **1000 V**  IFSM (8.3 ms half sine-wave) = **30 A**  IF(AV) at TA: 55°C = **1 A**  IR at 25°C = **10 µA**  **TJ, TSTG = -55 to 150 °C RθJA = 60 °C/W** | VRRM = **1000 V** VFM at 1 A = **1.2 V**  VRMS = **700 V**  VR = **1000 V**  IFSM (8.3 ms half sine-wave) = **30 A**  IO at TA: 55°C = **1 A**  IRM at 25°C = **5 µA**  **TJ = -65 to 125 °C** | VRRM = **1000 V** VF at 1 A = **1.2 V**  VRMS = **700 V**  VDC = **1000 V**  IFSM (8.3 ms half sine-wave) = **60 A**  IAV at TA: 55°C = **2 A**  IR at 25°C = **5 µA**  **TJ, TSTG = -65 to 150 °C RθJA = 60 °C/W** | VRRM = **100 V** VF at 10 mA = **1 V max.**  VR = **75 V**  IF(AV) = **150 mA**  IFSM at tp = 1 µA= **2 A**  IR at 25°C = **5 µA**  Ptot at 45 °C = 0.44 W  **TJ, TSTG = -65 to 150 °C RθJA = 350 °C/W** |

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| **HER303** |  |  |  |
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| **High Efficiency Rectifier Diode** |  |  |  |
| VRRM = **100 V** VF at 3 A = **1 V**  VRMS = **70 V**  VDC = **100 V**  IFSM (8.3 ms half sine-wave) = **150 A**  IO at TA: 50°C = **3 A**  IR at 25°C = **10 µA**  TJ, TSTG = **-65 to 150 °C** |  |  |  |
| **SLD18-018** | **TP6KE24CA** | **TPSMB20CA** |  |
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| **Bi-Directional TVS Diode** | **Bi-Directional TVS Diode** | **Bi-Directional TVS Diode** |  |
| VBR = **20 V min. / 22.1 max.**  VR = **18 V** VC = **29.2 V**  IPP = **147.7 A** IR at VR = **10 µA**  IFSM (8.3 ms half sine-wave) = **600 A**  PD at TL: 75°C = **8 W**  TJ, TSTG = **-55 to 175 °C** RθJA = **40 °C/W** | VBR = **22.8 V min. / 25.2 max.**  VR = **20.5 V** VC = **33.2 V**  IPP = **18.4 A** IR at VR = **1 µA**  PPPM by 10/1000 µA = **5 W**  PD at TL: 75°C = **5 W**  TJ, TSTG = **-55 to 175 °C** RuJA = **75 °C/W** | VBR =  **19 V min. / 21 max.**  VR = **17.1 V** VC = **27.7 V**  IPP = **22 A** IR at VR = **1 µA**  Max. temp. coefficient of VBR = **0.085 %/C**  PM(AV) at TL: 50°C = **5 W**  TJ, TSTG = **-55 to 175 °C** RθJA = **100 °C/W** |  |
| **1N5817** | **1N5818** | **1N5819** | **1N5822** |
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| **Schottky Barrier Rectifier Diode** | **Schottky Barrier Rectifier Diode** | **Schottky Barrier Rectifier Diode** | **Schottky Barrier Rectifier Diode** |
| VRRM = **20 V** VF at 1 A = **0.45 V**  VRSM = **24 V**  VR(RSM) = **14 V**  IFSM (half wave, s. phase 60 Hz) = **25 A**  IO at 55°C = **1 A**  IR at TA: 55°C= **1 mA**  TJ, TSTG = **-65 to 125 °C** RθJA = **80 °C/W** | VRRM = **30 V** VF at 1 A = **0.55 V**  VRSM = **36 V**  VR(RSM) = **21 V**  IFSM (half wave, s. phase 60 Hz) = **25 A**  IO at 55°C = **1 A**  IR at TA: 55°C= **1 mA**  TJ, TSTG = **-65 to 125 °C** RθJA = **80 °C/W** | VRRM = **40 V** VF at 1 A = **0.6 V**  VRSM = **48 V**  VR(RSM) = **28 V**  IFSM (half wave, s. phase 60 Hz) = **25 A**  IO at 55°C = **1 A**  IR at TA: 55°C= **1 mA**  TJ, TSTG = **-65 to 125 °C** RθJA = **80 °C/W** | VRRM = **40 V** VF at 1 A = **0.39 V**  VRSM = **48 V**  VR(RSM) = **28 V**  IFSM (half wave, s. phase 60 Hz) = **80 A**  IO at TA: 95°C = **3 A**  IR at TA: 25°C= **2 mA**  TJ, TSTG = **-65 to 125 °C**  RθJA = **28 °C/****W** |
| **SR3100** | **SR5100** |  |  |
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| **Schottky Barrier Rectifier Diode** | **Schottky Barrier Rectifier Diode** |  |  |
| VRRM = **100 V max.** VF at 3 A = **0.83 V**  VRWM = **100 V**  VDC = **100 V max.**  IFSM (8.3 ms half sine-wave) = **80 A**  IAV = **3 A**  IR at TA: 25°C= **0.3 mA**  TJ, TSTG = **-50 to 150 °C**  RθJA = **25 °C/W** | VRRM = **100 V** VFM at 5 A = **0.85 V**  VRWM = **100 V**  VR(RMS) = **70 V**  IFSM (8.3 ms half sine-wave) = **150 A**  IO = **5 A**  IRM at TA: 25°C= **0.5 mA**  TJ, TSTG = **-65 to 125 °C**  RθJA = **25 °C/W** |  |  |
| **SB560** |  |  |  |
|  |  |  |  |
| **Schottky Barrier Rectifier Diode** |  |  |  |
| VRRM = **60 V** VF at 5 A = **0.65 V**  VRMs = **42 V** VDC = **60 V**  IF(AV) = **5 A**  IFSM (8.3 ms half sine-wave) = **220 A**  **TJ, TSTG = -65 to 150 °C RθJA = 25 °C/W** |  |  |  |